L Number	Hits	Search Text	DB	Time stamp
1	181	(thin adj film adj transistors) near10	USPAT;	2003/04/14 13:26
		(pixel adj (unit or region or area))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
2	o	(signal adj lines) near10 (crossing or	USPAT;	2003/04/14 13:28
_		perpendicular) near10 (gate adj lines) and	US-PGPUB;	
		((thin adj film adj transistors) near10	EPO; JPO;	
		(pixel adj (unit or region or area)))	DERWENT;	
		(IBM_TDB	2002/04/14 12:00
3	0	(signal adj lines) near10 (crossing or perpendicular) near10 (scan adj lines) and	USPAT; US-PGPUB;	2003/04/14 13:29
		((thin adj film adj transistors) near10	EPO; JPO;	
		(pixel adj (unit or region or area)))	DERWENT;	
			IBM_TDB	
6	2	6043145.did.	USPAT;	2003/04/14 13:35
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	22	"349" and (first adj photoresist adj	USPĀT;	2003/04/11 13:32
		layer)	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	23	"349" and (second adj photoresist adj	USPAT;	2003/04/11 13:33
		layer)	US-PGPUB;	•
		•	EPO; JPO;	
			DERWENT;	
·	2	 "349" and (third adj photoresist adj	IBM_TDB USPAT;	2003/04/11 13:34
_	2	layer)	US-PGPUB;	2003/04/11 13.54
		20,027	EPO; JPO;	
			DERWENT;	.
	_		IBM_TDB	0000/04/41 40 40
_	2	("349" and (first adj photoresist adj layer)) and ("349" and (second adj	USPAT; US-PGPUB;	2003/04/11 13:49
		photoresist adj layer)) and ("349" and	EPO; JPO;	-
		(third adj photoresist adj layer))	DERWENT;	
			IBM_TDB	
_	1811	first adj photoresist adj layer	USPAT;	2003/04/11 13:51
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1873	second adj photoresist adj layer	USPAT;	2003/04/11 13:52
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
-	365	third adj photoresist adj layer	USPAT;	2003/04/11 13:53
		· -	US-PGPUB;	
1			EPO; JPO;	
			DERWENT; IBM TDB	
_	264	(first adj photoresist adj layer) and	USPAT;	2003/04/11 13:54
	201	(second adj photoresist adj layer) and	US-PGPUB;	
		(third adj photoresist adj layer)	EPO; JPO;	
			DERWENT;	
	1	 (first adj photoresist adj layer) near10	IBM_TDB USPAT;	2003/04/11 13:57
	1	cover near10 pixel	US-PGPUB;	
}			EPO; JPO;	
			DERWENT;	
		(since add whotomorist add larger) manual	IBM_TDB USPAT;	2003/04/11 13:58
-	0	(first adj photoresist adj layer) near10 above near10 pixel	USPAT; US-PGPUB;	2003/04/11 13.50
		anove Heatto biver	EPO; JPO;	
1			DERWENT;	
			IBM TDB	

-	1	(first adj photoresist adj layer) near10	USPAT;	2003/04/11 14:06
		over near10 pixel	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	+
	412	(contact or hole or opening or aperture)	USPAT;	2003/04/11 14:08
_	413	near10 (first adj photoresist adj layer)	US-PGPUB;	2003/04/11 14.08
		nearro (litse ad) photoresist adj rayer,	EPO; JPO;	
			DERWENT;	
			IBM TDB	
1_	399	(contact or hole or opening or aperture)	USPAT;	2003/04/11 14:09
	333	near10 (second adj photoresist adj layer)	US-PGPUB;	2003/01/11 11103
		neurro (become da) photoreoro da) rajor,	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	65	(contact or hole or opening or aperture)	USPAT;	2003/04/11 14:10
		near10 (third adj photoresist adj layer)	US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	26		USPĀT;	2003/04/11 14:14
		near10 (first adj photoresist adj layer))	US-PGPUB;	
		and ((contact or hole or opening or	EPO; JPO;	
		aperture) near10 (second adj photoresist	DERWENT;	
		adj layer)) and ((contact or hole or	IBM_TDB	
		opening or aperture) near10 (third adj		
		photoresist adj layer))		
-	699	(349/43).CCLS.	USPAT;	2003/04/11 14:15
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		240/42	IBM_TDB	2002/04/11 14:10
-	1		USPAT;	2003/04/11 14:18
		layer) near10 (hole or opening or aperture	US-PGPUB;	
		or contact))	EPO; JPO; DERWENT;	
			IBM TDB	
	0	349/43 and ((second adj photoresist adj	USPAT;	2003/04/11 14:19
_		layer) near10 (hole or opening or aperture	US-PGPUB;	2003/04/11 13:13
		or contact))	EPO; JPO;	
		Of contact)	DERWENT;	
			IBM TDB	
_	n	(first adj photoresist adj layer) near10	USPĀT;	2003/04/11 14:21
		expos\$6 near10 (drain adj electrode)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	N=====	USPĀT;	2003/04/11 14:22
1	1	exposing near10 (drain adj electrode)	US-PGPUB;	
1	1		EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	0000 (04 /11 11 11
-	0	(second adj photoresist adj layer) near10	USPAT;	2003/04/11 14:22
		exposing near10 (drain adj electrode)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		161	IBM_TDB	2003/04/11 14:24
1-	1	(first adj photoresist adj layer) near10	USPAT;	2003/04/11 14:24
		exposing near10 (thin adj film adj	US-PGPUB; EPO; JPO;	
		transistor)	DERWENT;	
	1		IBM TDB	
_	1	(photoresist adj layers) near10 expos\$6	USPAT;	2003/04/11 14:34
-	1	near10 (drain adj electrode)	US-PGPUB;	
		indulto (alain adj cicociode)	EPO; JPO;	
			DERWENT;	
	1		IBM TDB	
4	1	1		

-	2	(photoresist adj layers) near10 expos\$6	USPAT;	2003/04/11 14:29
1	1	near10 (thin adj film adj transistor)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		16.	IBM_TDB	2222/24/24
-	0	(first adj photoresist) near10 expos\$6	USPAT;	2003/04/11 14:31
		near10 (drain adj electrode)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
} -	2	(==== + -:-;)	USPAT;	2003/04/11 14:31
		near10 (thin adj film adj transistor)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		6062652 314	IBM_TDB	0000/04/11 14 40
-	2	6063653.did.	USPAT;	2003/04/11 14:40
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1	/6:	IBM_TDB	2002/04/11 14 42
-	1	, ,	USPAT;	2003/04/11 14:42
		near10 (pixel)	US-PGPUB;	•
			EPO; JPO; DERWENT;	
	7	(first add photograph) page 10 (above an	IBM_TDB USPAT;	2003/04/11 14:43
-	/	(first adj photoresist) near10 (above or		2003/04/11 14:43
1		over or overlay) near10 (pixel)	US-PGPUB; EPO; JPO;	_
			DERWENT;	_
			IBM TDB	
1_	8	(second adj photoresist) near10 (above or	USPAT;	2003/04/11 14:45
1	•	over or overlay) near10 (pixel)	US-PGPUB;	2003/04/11 14.45
		Over or overray) hearro (pixer)	EPO; JPO;	
			DERWENT;	
			IBM TDB	-
_	0	(third adj photoresist) near10 (above or	USPAT;	2003/04/11 14:57
		over or overlay) near10 (pixel)	US-PGPUB;	2003/04/11 11:3/
		Over or overlay, nearly	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	6	((first adj photoresist) near10 (above or	USPĀT;	2003/04/11 16:50
	_	over or overlay) near10 (pixel)) and	US-PGPUB;	
		((second adj photoresist) near10 (above or	EPO; JPO;	
		over or overlay) near10 (pixel))	DERWENT;	
			IBM TDB	
-	1	,	USPĀT;	2003/04/11 14:58
		on) near10 (pixel)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	-		IBM_TDB	
-	861	photoresist near10 expos\$6 near10 drain	USPAT;	2003/04/11 15:06
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/04/44 15 55
-	35	(first adj photoresist) near10 expos\$6	USPAT;	2003/04/11 15:00
		near10 drain	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	-	(second adj photoresist) near10 expos\$6	IBM_TDB USPAT;	2003/04/11 15:01
1-	54	near10 drain	US-PGPUB;	5003/04/TT T3:0T
		HEALIU GLAIN	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	10	(photoresist near10 expos\$6 near10 drain)	USPAT;	2003/04/11 15:01
		and ((first adj photoresist) near10	US-PGPUB;	
	1	expos\$6 near10 drain) and ((second adj	EPO; JPO;	
		photoresist) near10 expos\$6 near10 drain)	DERWENT;	
			IBM TDB	
	I	I		

-	932	(first adj photoresist) near10 (hole or opening or aperture or contact or slit or via)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/11 15:09
-	953	(second adj photoresist) near10 (hole or opening or aperture or contact or slit or via)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/11 15:11
_	152	(third adj photoresist) near10 (hole or opening or aperture or contact or slit or via)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/11 15:11
-	50	((first adj photoresist) near10 (hole or opening or aperture or contact or slit or via)) and ((second adj photoresist) near10 (hole or opening or aperture or contact or slit or via)) and ((third adj photoresist) near10 (hole or opening or aperture or contact or slit or via))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/11 15:25
-	89		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/11 15:29
_	1	holes near10 (photoresist adj (films or layers)) near10 expos\$6 near10 (drain adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/11 15:29
_	0	holes near10 (photoresist adj (films or layers)) near10 expos\$6 near10 (TFT)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/11 15:30
-	0	(holes or vias or contacts or apertures or slits or openings) near10 (photoresist adj (films or layers)) near10 expos\$6 near10 (TFT)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/11 15:31
-	1	(holes or vias or contacts or apertures or slits or openings) near10 (photoresist adj (films or layers)) near10 expos\$6 near10 (drain adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/11 15:39
_	19	photoresist near10 exposing near10 (drain adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/11 15:51
_	1	photoresist near10 holes near10 exposing near10 (drain adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/11 15:44
_	4	349/43 and (photoresist adj (films or layers))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/11 15:56
_	1	(photoresist adj (films or layers)) near10 expos\$6 near10 (drain adj electrode) near10 (through adj hole)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/11 15:57

_	0	<pre>(photoresist adj (films or layers)) near10 contact near10 (drain adj electrode)</pre>	USPAT; US-PGPUB;	2003/04/11 15:5	58
		near10 (hole)	EPO; JPO; DERWENT;		
_	0	(photoresist adj (films or layers)) near10	IBM_TDB USPAT;	2003/04/11 15:5	59
		opening near10 (drain adj electrode)	US-PGPUB; EPO; JPO; DERWENT;		
	0	(photoresist adj (films or layers)) near10	IBM_TDB USPAT;	2003/04/11 16:0	00
_		showing near10 (drain adj electrode)	US-PGPUB; EPO; JPO;	2003/04/11 10.0	50
			DERWENT; IBM TDB		
-	2	<pre>(photoresist adj (films or layers)) near10 expos\$6 near10 (thin adj film adj</pre>	USPAT; US-PGPUB;	2003/04/11 16:0	03
		transistor)	EPO; JPO; DERWENT;		
-	0	(photosensitive adj (films or layers)) near10 expos\$6 near10 (drain adj	IBM_TDB USPAT; US-PGPUB;	2003/04/11 16:0	04
		electrode)	EPO; JPO; DERWENT;		
-	0	,	IBM_TDB USPAT;	2003/04/11 16:0	04
		near10 (drain adj electrode)	US-PGPUB; EPO; JPO;		,
	15	(photosensitive) near10 expos\$6 near10	DERWENT; IBM_TDB USPAT;	2003/04/11 16:0	0.5
		(drain adj electrode)	US-PGPUB; EPO; JPO;		
	_		DERWENT; IBM_TDB		
_	7	(passivation adj layers) near10 expos\$6 near10 (drain adj electrode)	USPAT; US-PGPUB; EPO; JPO;	2003/04/11 16:0) /
			DERWENT; IBM TDB	•	
_	11	(first adj passivation adj layer) near10 expos\$6 near10 (drain adj electrode)	USPAT; US-PGPUB;	2003/04/11 16:0	98
			EPO; JPO; DERWENT; IBM TDB		
-	7	(second adj passivation adj layer) near10 expos\$6 near10 (drain adj electrode)	USPAT; US-PGPUB;	2003/04/11 16:2	23
		in the second of	EPO; JPO; DERWENT;		
-	1	, , , , , , , , , , , , , , , , , , , ,	IBM_TDB USPAT;	2003/04/11 16:1	10
		expos\$6 near10 (drain adj electrode)	US-PGPUB; EPO; JPO; DERWENT;		
_	6	((first adj passivation adj layer) near10	IBM_TDB USPAT;	2003/04/11 16:1	15
		expos\$6 near10 (drain adj electrode)) and ((second adj passivation adj layer) near10 expos\$6 near10 (drain adj electrode))	US-PGPUB; EPO; JPO; DERWENT;		
-	0	(first adj photosensitive adj (layer or	IBM_TDB USPAT;	2003/04/11 16:1	13
		<pre>film)) near10 expos\$6 near10 (drain adj electrode)</pre>	US-PGPUB; EPO; JPO; DERWENT;		
_	0	(first adj resin adj (layer or film))	IBM TDB USPAT;	2003/04/11 16:1	15
		near10 expos\$6 near10 (drain adj electrode)	US-PGPUB; EPO; JPO;		
			DERWENT; IBM_TDB		

_	0	(first adj photoresist) near10 (drain adj contact adj hole)	USPAT; US-PGPUB; EPO; JPO;	2003/04/11 16:16
			DERWENT; IBM TDB	
	0	(first adj photoresist) near10 cover near10 (first adj pixel adj (group or area))	USPĀT; US-PGPUB; EPO; JPO;	2003/04/11 16:27
			DERWENT; IBM TDB	
-	0	(first adj photoresist) near10 cover near10 (first adj pixel)	USPĀT; US-PGPUB; EPO; JPO;	2003/04/11 16:28
			DERWENT; IBM_TDB	
_	1	<pre>(photoresist adj (films or layers)) near10 (pixel adj areas)</pre>	USPAT; US-PGPUB; EPO; JPO;	2003/04/11 16:29
			DERWENT; IBM_TDB	
_	0	<pre>(photoresist adj (films or layers)) near10 (pixel adj groups)</pre>	USPAT; US-PGPUB; EPO; JPO;	2003/04/11 16:31
			DERWENT; IBM_TDB	
-	1	(photoresist adj (films or layers)) near10 cover near10 pixel	USPAT; US-PGPUB; EPO; JPO;	2003/04/11 16:33
			DERWENT; IBM_TDB	
-	152	first adj pixel adj (group or area)	USPAT; US-PGPUB; EPO; JPO;	2003/04/11 16:35
			DERWENT; IBM_TDB	-
-	106	second adj pixel adj (group or area)	USPAT; US-PGPUB; EPO; JPO;	2003/04/11 16:36
41 A A A A A A A A A A A A A A A A A A A			DERWENT; IBM_TDB	
_	21	third adj pixel adj (group or area)	USPAT; US-PGPUB; EPO; JPO;	2003/04/11 16:36
			DERWENT; IBM TDB	
-	14	(first adj pixel adj (group or area)) and (second adj pixel adj (group or area)) and (third adj pixel adj (group or area))	USPĀT; US-PGPUB; EPO; JPO;	2003/04/11 16:41
		(third ad) pixer ad) (group or area))	DERWENT; IBM TDB	
_	2	20020075435.did.	USPAT; US-PGPUB;	2003/04/11 16:41
			EPO; JPO; DERWENT; IBM TDB	
-	2	4673253.did.	USPAT; US-PGPUB;	2003/04/11 16:53
			EPO; JPO; DERWENT; IBM TDB	
_	12	(first adj photoresist) near10 pixel	USPAT; US-PGPUB; EPO; JPO;	2003/04/11 16:54
			DERWENT; IBM_TDB	
_	27	(second adj photoresist) near10 pixel	USPĀT; US-PGPUB; EPO; JPO;	2003/04/11 16:55
	,		DERWENT; IBM_TDB	

-	7	(third adj photoresist) near10 pixel	USPAT; US-PGPUB; EPO; JPO;	2003/04/11 16:55
			DERWENT; IBM_TDB	
-	5	<pre>((first adj photoresist) near10 pixel) and ((second adj photoresist) near10 pixel) and ((third adj photoresist) near10 pixel)</pre>	USPAT; US-PGPUB; EPO; JPO;	2003/04/11 17:11
_	0	(pixel adj area) near10 cover near10	DERWENT; IBM_TDB USPAT;	2003/04/11 17:13
		(photoresist adj (films or layers))	US-PGPUB; EPO; JPO; DERWENT; IBM TDB	
_	0	<pre>(pixel adj area) near10 under near10 (photoresist adj (films or layers))</pre>	USPAT; US-PGPUB; EPO; JPO;	2003/04/11 17:14
		(rival adi vait) maari0 yadan maari0	DERWENT; IBM_TDB USPAT;	2003/04/11 17:14
_	0	<pre>(pixel adj unit) near10 under near10 (photoresist adj (films or layers))</pre>	US-PGPUB; EPO; JPO; DERWENT;	2003/04/11 17.14
_	0	(pixel adj group) near10 under near10 (photoresist adj (films or layers))	IBM_TDB USPAT; US-PGPUB;	2003/04/11 17:14
			EPO; JPO; DERWENT; IBM TDB	
_	0	<pre>(pixel adj section) near10 under near10 (photoresist adj (films or layers))</pre>	USPAT; US-PGPUB; EPO; JPO;	2003/04/11 17:15
_	0	(pixel) near10 under near10 (photoresist	DERWENT; IBM_TDB USPAT; US-PGPUB;	2003/04/11 17:15
	i i	adj (films or layers))	EPO; JPO; DERWENT;	
-	0	(pixel) near10 under near10 (photosensitive adj (films or layers))	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/04/11 17:19
_	0	(pixel) near10 under near10 (etching adj	DERWENT; IBM_TDB USPAT;	2003/04/11 17:20
		(films or layers))	US-PGPUB; EPO; JPO; DERWENT; IBM TDB	
_	0	(etching adj (films or layers)) near10 over near10 pixels	USPAT; US-PGPUB; EPO; JPO;	2003/04/11 17:21
_	1	etchant near10 over near10 pixels	DERWENT; IBM_TDB USPAT;	2003/04/11 17:26
			US-PGPUB; EPO; JPO; DERWENT;	
_	1	(mask adj layers) near10 over near10 pixels	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/04/11 17:35
	0	(resist adj layers) near10 over near10	DERWENT; IBM_TDB USPAT;	2003/04/11 17:35
_		pixels	US-PGPUB; EPO; JPO; DERWENT;	2000,01,11 1,.33
			IBM TDB	

	,	,		
-	0	(pixel adj areas) near10 (resist adj	USPAT;	2003/04/11 17:36
		layers)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	1
	5272	 (pixel) near10 under ((first adj	IBM_TDB USPAT;	2003/04/11 17:38
-	3272	photoresist adj layer) near10 above near10	US-PGPUB;	2003/04/11 17:38
		pixel) near10 (resist adj layers)	EPO; JPO;	
		pixel, healto (lesise adj layels,	DERWENT;	į
			IBM TDB	
_	0	(pixel) near10 under near10 (resist adj	USPAT;	2003/04/11 17:39
		layers)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	1
_	0	(pixel) near10 under near10 (platings)	USPAT;	2003/04/11 17:39
			US-PGPUB;	
			EPO; JPO;	i
			DERWENT;	
			IBM_TDB	
-	0	(pixel) near10 under near10 (DFRs)	USPAT;	2003/04/11 17:40
			US-PGPUB;	-
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	0000/01/01 00 00
_	0	((multiple or plural) adj (pixel adj	USPAT;	2003/04/14 09:31
		layers)) near10 (contact or hole or	US-PGPUB;	
		aperture or slit or opening)	EPO; JPO;	
			DERWENT;	
	2	//multiple or plural) add /pivol add	IBM_TDB USPAT;	2003/04/14 09:33
_	2	((multiple or plural) adj (pixel adj	US-PGPUB;	2003/04/14 09:33
!	ŀ	layers))	EPO; JPO;	
			DERWENT;	
			IBM TDB	
	2	((multiple or plural) near10 (pixel adj	USPAT;	2003/04/14 09:36
		layers))	US-PGPUB;	2000,00, 22
			EPO; JPO;	
			DERWENT;	1
			IBM TDB	
-	2	multiple adj pixel adj layers	USPĀT;	2003/04/14 09:40
			US-PGPUB;	
			EPO; JPO;	1
			DERWENT;	
			IBM_TDB	0000 (5: (5: 5: 5: 5: 5: 5: 5: 5: 5: 5: 5: 5: 5: 5
-	0	plural adj pixel adj layers	USPAT;	2003/04/14 09:41
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		/	IBM_TDB	2002/04/14 00:42
-	3	(spacer or protrusion) near10 pierc\$6	USPAT;	2003/04/14 09:42
		near10 layers	US-PGPUB; EPO; JPO;	
			DERWENT;	
	1		IBM TDB	
_	6	(spacer or pillar) near10 pierc\$6 near10	USPAT;	2003/04/14 09:49
_		layers	US-PGPUB;	2000/01/14 07.47
]	Layers	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	53	pixel adj layers	USPAT;	2003/04/14 10:18
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	(pixel adj layers) near10 expos\$6 near10	USPĀT;	2003/04/14 09:54
	1	(drain adj electrode)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	

		L(: 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1	TTODAM.	2002/04/14 00 54
-	0	(pixel adj layers) nearl0 (drain adj	USPAT; US-PGPUB;	2003/04/14 09:54
		electiode,	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	(pixel adj layers) near10 expos\$6 near10	USPAT;	2003/04/14 09:57
•		(data adj line)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	(photoresist adj layers) near10 expos\$6	USPAT;	2003/04/14 09:58
		near10 (data adj line)	US-PGPUB;	
]			EPO; JPO;	
			DERWENT;	
	0	(-b-t-mash add lawara) masu10 awas66	IBM_TDB	2003/04/14 09:58
_	U	(photomask adj layers) near10 expos\$6 near10 (data adj line)	USPAT; US-PGPUB;	2003/04/14 09:36
		Hearro (data adj rine)	EPO; JPO;	
			DERWENT;	
		'	IBM TDB	
_	0	(resist adj layers) near10 (pixel adj	USPAT;	2003/04/14 10:00
		layers)	US-PGPUB;	
		_	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	0	(resist adj layers) near10 (exposing)	USPAT;	2003/04/14 10:00
		near10 (drain adj electrode)	US-PGPUB;	
1			EPO; JPO;	
			DERWENT; IBM TDB	
_	3	(first adj insulating adj layer) near10	USPAT;	2003/04/14 10:24
-	,	cover\$6 Near10 (pixel adj electrode)	US-PGPUB;	2003/04/14 10.24
,		covery means (piner day electrode)	EPO; JPO;	
			DERWENT;	
			IBM TDB	-
-	13	(second adj insulating adj layer) near10	USPAT;	2003/04/14 10:23
		cover\$6 Near10 (pixel adj electrode)	US-PGPUB;	
			EPO; JPO;	-
İ			DERWENT;	
	,	 (third adj insulating adj layer) near10	IBM_TDB USPAT;	2003/04/14 10:23
-	3	cover\$6 Near10 (pixel adj electrode)	US-PGPUB;	2003/04/14 10:23
		coverso hearto (pixer ad) electrode;	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	((first adj insulating adj layer) near10	USPAT;	2003/04/14 10:23
:		cover\$6 Near10 (pixel adj electrode)) and	US-PGPUB;	
		((second adj insulating adj layer) near10	EPO; JPO;	
1		cover\$6 Near10 (pixel adj electrode)) and	DERWENT;	
		((third adj insulating adj layer) near10	IBM_TDB	
	1.5	cover\$6 Near10 (pixel adj electrode))	IICDAT.	2003/04/14 10:25
_	17	(first adj insulating adj (layer or film)) near10 cover\$6 near10 (pixel adj	USPAT; US-PGPUB;	2003/04/14 10:23
		electrode)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	33	(second adj insulating adj (layer or	USPAT;	2003/04/14 10:25
		film)) near10 cover\$6 near10 (pixel adj	US-PGPUB;	
		electrode)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/04/14 12 26
_	6		USPAT;	2003/04/14 10:26
		near10 cover\$6 near10 (pixel adj	US-PGPUB; EPO; JPO;	
		erectrode)	DERWENT;	
			IBM TDB	
I	I			

-	1		USPAT;	2003/04/14 10:37
		film)) near10 cover\$6 near10 (pixel adj	US-PGPUB;	
		electrode)) and ((second adj insulating	EPO; JPO;	
		adj (layer or film)) near10 cover\$6 near10	DERWENT;	
1		(pixel adj electrode)) and ((third adj	IBM_TDB	
		insulating adj (layer or film)) near10		
		cover\$6 near10 (pixel adj electrode))		
-	1		USPAT;	2003/04/14 10:42
		(insulating adj layers) near10 connect\$6	US-PGPUB;	
1		near10 (drain or data)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	10		USPAT;	2003/04/14 10:44
		near10 connect\$6 near10 (drain or data)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	196		USPAT;	2003/04/14 10:46
		near10 (insulating adj layers)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	0	\	USPAT;	2003/04/14 10:47
		near10 (insulating adj layers)near10	US-PGPUB;	
		connect near10 (drain electrode)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	12		USPAT;	2003/04/14 11:06
	İ	near10 (insulating adj layers)near10	US-PGPUB;	
		(drain electrode)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	1 / 1	USPAT;	2003/04/14 11:11
		film)) near10 between near10 (first adj	US-PGPUB;	-
		insulating adj (film or layer)) near10 TFT	EPO; JPO;	
			DERWENT;	
ì			IBM_TDB	2002/04/14 11.52
-	22		USPAT;	2003/04/14 11:53
		film)) near10 between near10 (first adj	US-PGPUB;	
		insulating adj (film or layer))	EPO; JPO; DERWENT;	
	_	/51 /5:]]	IBM_TDB USPAT;	2003/04/14 11:14
-	0	(first adj insulating adj (film or layer))		2003/04/14 11:14
		near10 cover near10 (first adj pixel)	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	46	(signal adj lines) near10 (crossing or	USPAT;	2003/04/14 13:34
-	40	perpendicular) near10 (gate adj lines)	US-PGPUB;	2000,04/14 10.04
		Perpendicular, hearto (gate ad) lines/	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	134	 switching near10 (pixel adj area)	USPAT;	2003/04/14 11:56
-	134	switching hearto (biver and area)	US-PGPUB;	2000,04,14 11.00
			EPO; JPO;	
			DERWENT;	
ĺ	1		IBM TDB	
_	0	((signal adj lines) near10 (crossing or	USPAT;	2003/04/14 11:56
-		perpendicular) near10 (gate adj lines))	US-PGPUB;	2000/04/14 11:00
1	ļ	and (switching near10 (pixel adj area))	EPO; JPO;	
		and (switching hearing (pixer ad) area))	DERWENT;	
			IBM TDB	
_	411	switching near10 (pixel adj (area or unit	USPAT;	2003/04/14 11:57
1 -	411	or region))	US-PGPUB;	
]		OI IOGION//	EPO; JPO;	
1			DERWENT;	
			IBM TDB	
Ļ	1			I

_	0	((signal adj lines) near10 (crossing or	USPAT;	2003/04/14 11:57
		perpendicular) near10 (gate adj lines))	US-PGPUB;	
		and (switching near10 (pixel adj (area or	EPO; JPO;	
		unit or region)))	DERWENT;	
			IBM_TDB	
-	82	switch near10 (pixel adj (area or unit or	USPAT;	2003/04/14 11:58
		region))	US-PGPUB;	
		-	EPO; JPO;	·
			DERWENT;	
		,	IBM TDB	!
-	0	((signal adj lines) near10 (crossing or	USPĀT;	2003/04/14 13:24
		perpendicular) near10 (gate adj lines))	US-PGPUB;	
		and (switch near10 (pixel adj (area or	EPO; JPO;	
	ĺ	unit or region)))	DERWENT;	
		-	IBM_TDB	